

Thursday, February 17, 2022 2:27 PM

↓
deform

② Fabrication - Aspects

Silicon based
Piezo-resistor

Water ← (Silica)
↑
high change in the
resistance

D

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SIMI - L-10
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Piezoresistor → very thin film
(Piezo-resistive sensor)
↓
deform

① Device - Aspects
② Fabrication - Aspects

Stress
strain
fluid flow
inertial
Shear stress
acceleration

deform

Silicon based Piezo-resistor

free Torque
strain
flow aerodynamics
viscosity
→ blood flow

Chemical reactive

Water ← (Silica)
↑
high change in the resistance

Silicon
↓
SiO₂



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Fluid flow
Inertial
Shear stress

Silicon based
Piezo-resistor

high change in the
resistance

acceleration
free Torque
strain
flow
viscosity
aerodynamics
to blood flow
Chemical
reactive

(i) Strain Gauge → higher sensitivity 50 times metal
semiconductor (Silicon)

3 metal
ciment
Si
metal
ciment



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13:29

1:09:55



ENG
IN

9:58 AM
3/3/2022

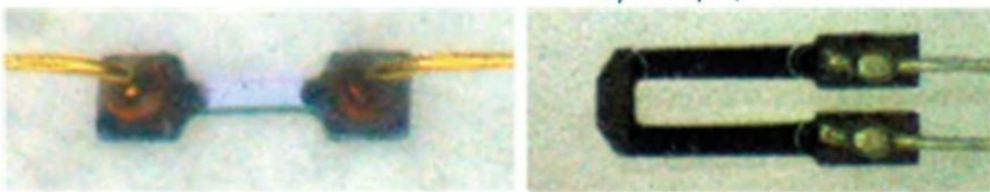
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↶ ↷ Eraser Pencil Highlighter Ink Shapes Ink to Shape

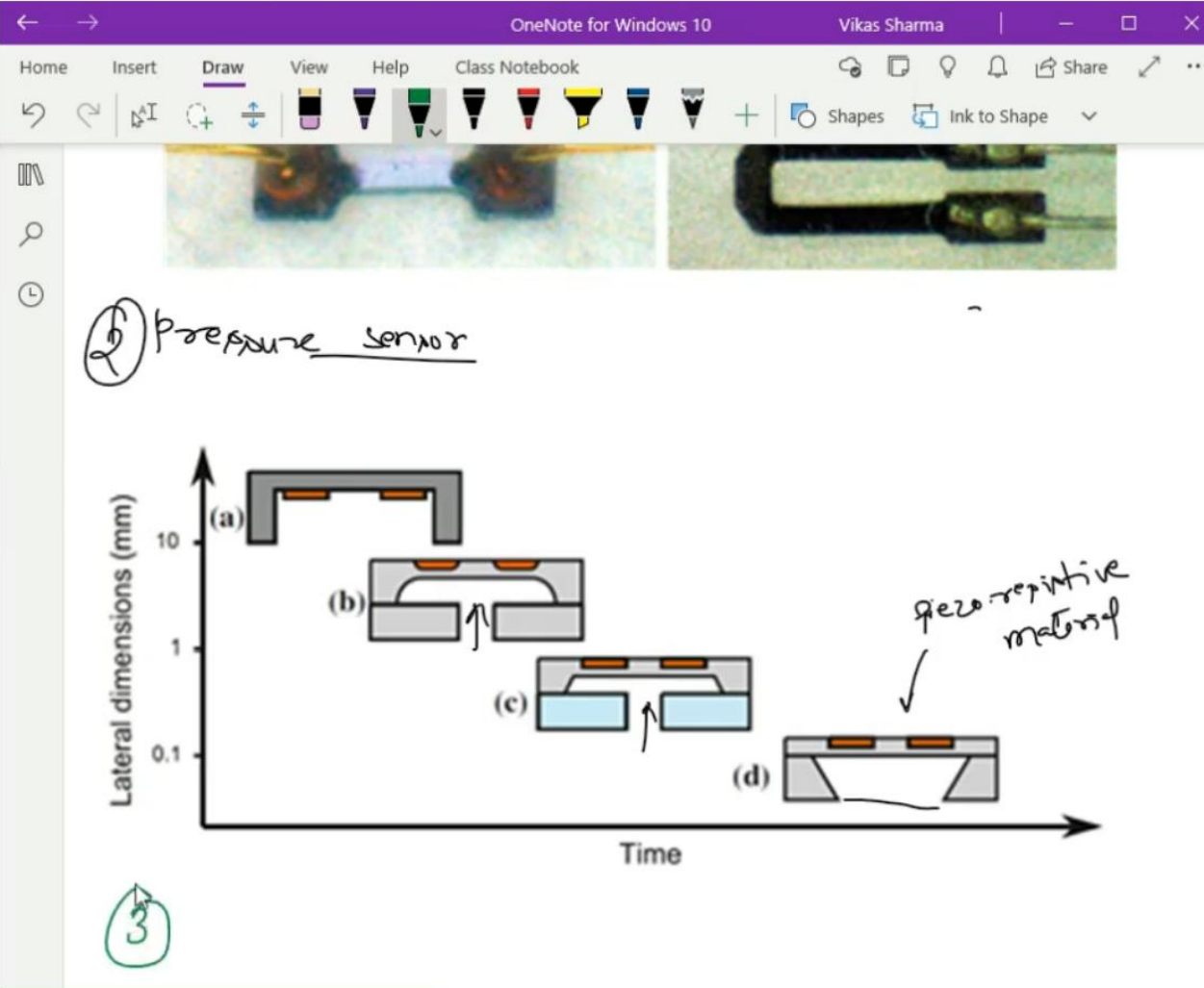
① Strain Gauge → higher sensitivity 50 times metal
 semiconductor (Silicon)

Diagram labels: Si, 3 metal, cement, metal

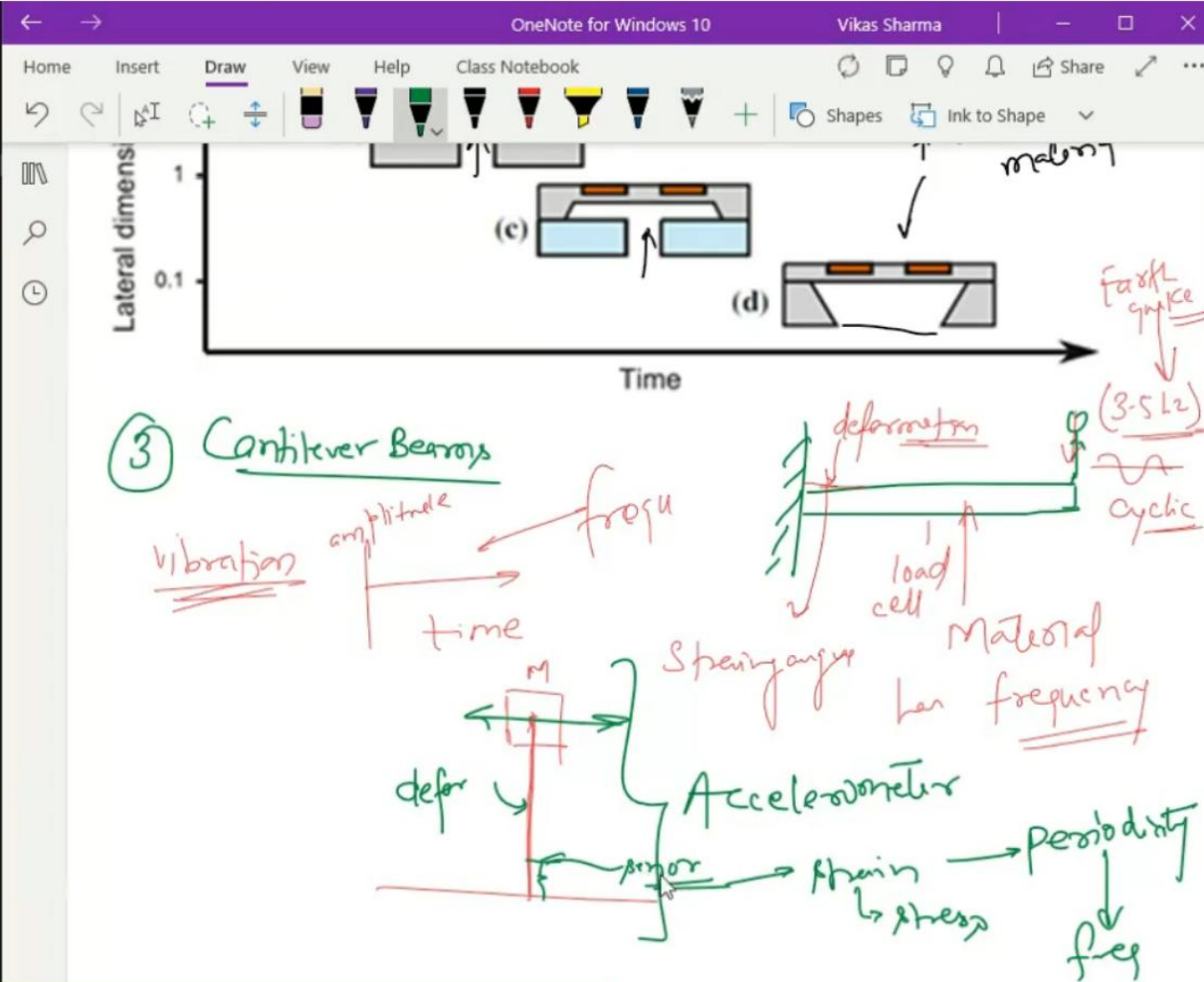


② Pressure sensor

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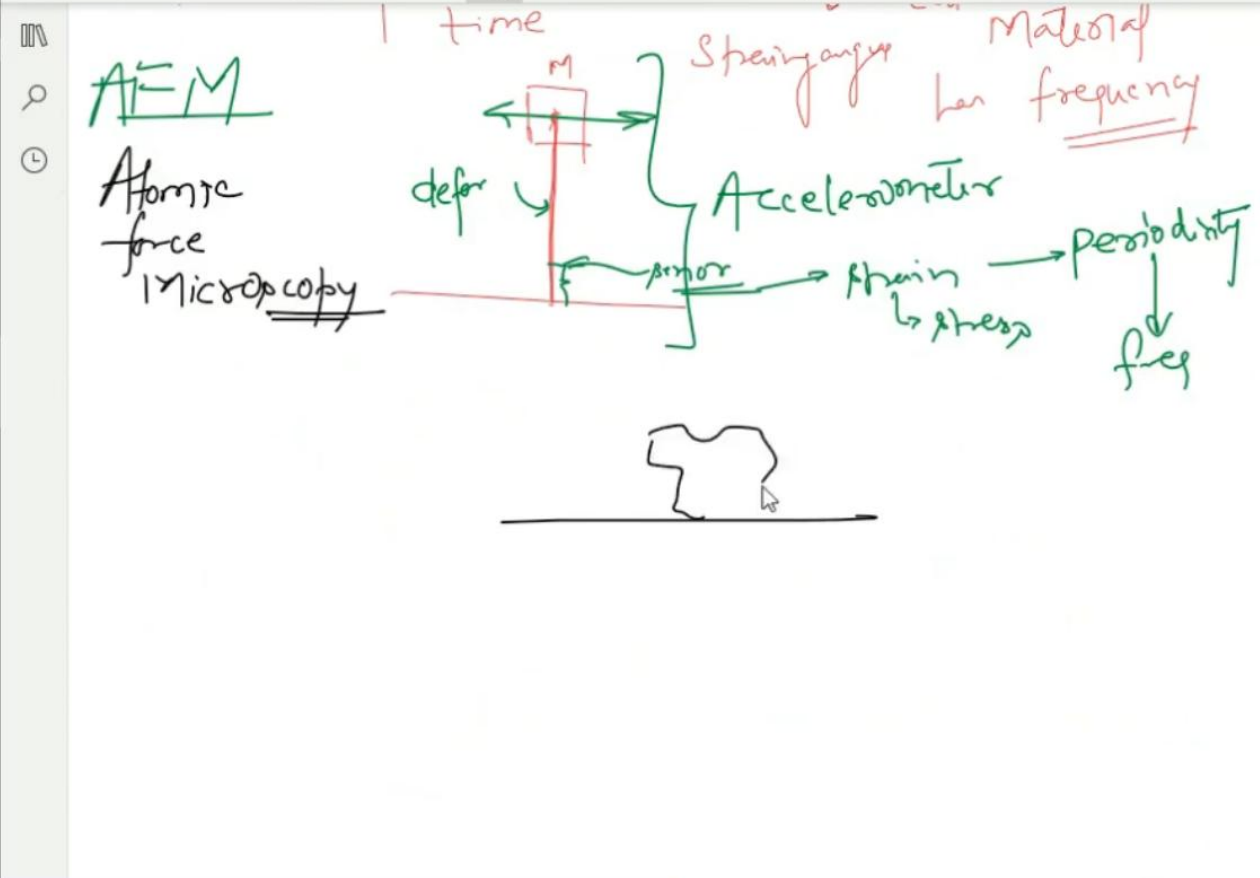
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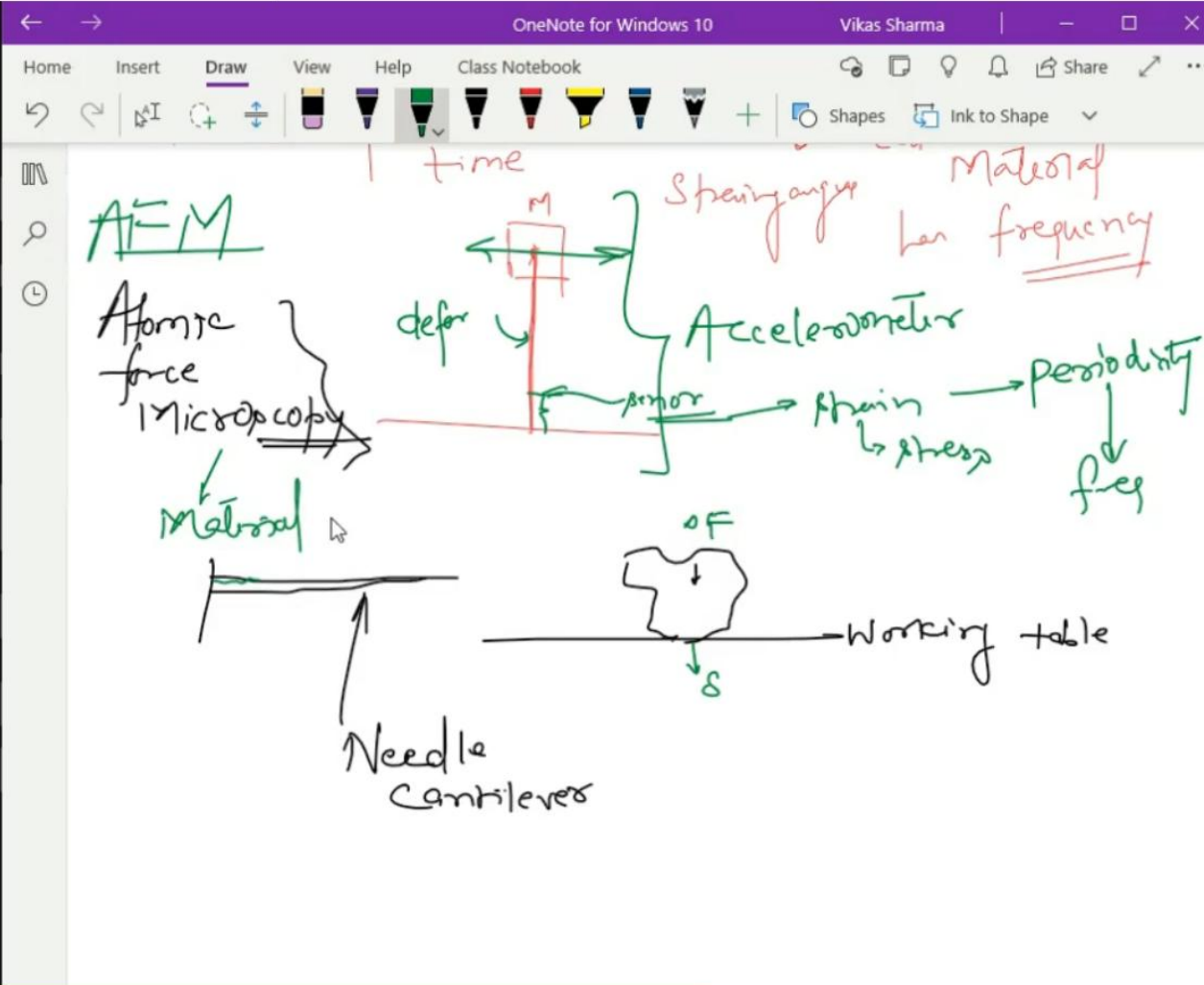


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Needle Cantilevers Metal Working table Silicon wafers brittle fragile

accelerometer vibration response speed change in velocity

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Shapes Ink to Shape

Gyroscopes

accelerometer
vibration
Response speed
change in velocity

fragile

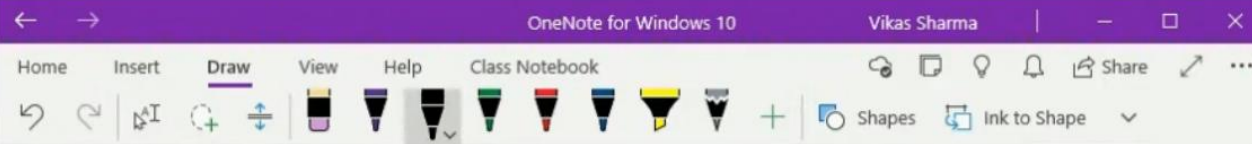
Automotive, military applications
Guiding & Sensing, STM

J

JANME JAYSINGH CHAUHAN

toxic

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Fabrication Aspect (Doping) → dopant concentration

- Ion implantation
- Diffusion
- Epitaxy



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Fabrication Aspect (Doping) → dopant concentration


- Ion implantation → single piece
- Diffusion → batch process
- Epitaxy → $HCl \rightarrow Si$

Silicon wafer

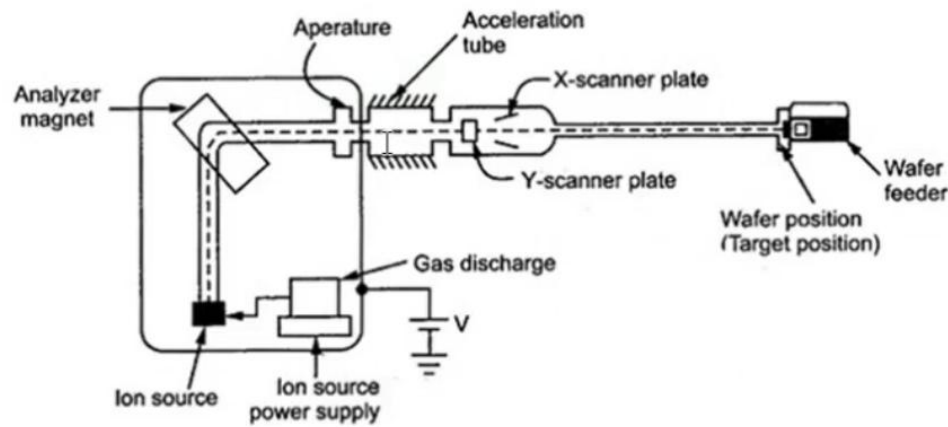
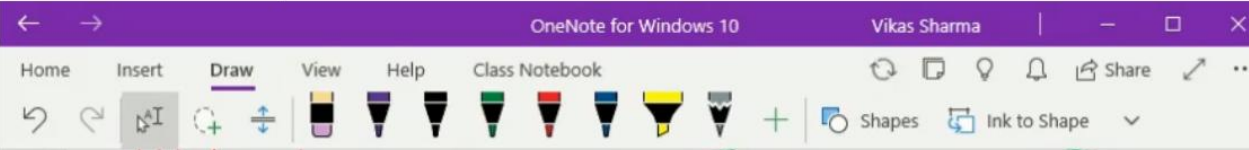
- Boron
- Arsenic
- Phosphorus

[Silicon wafer] ← dope

→ piezoresistor



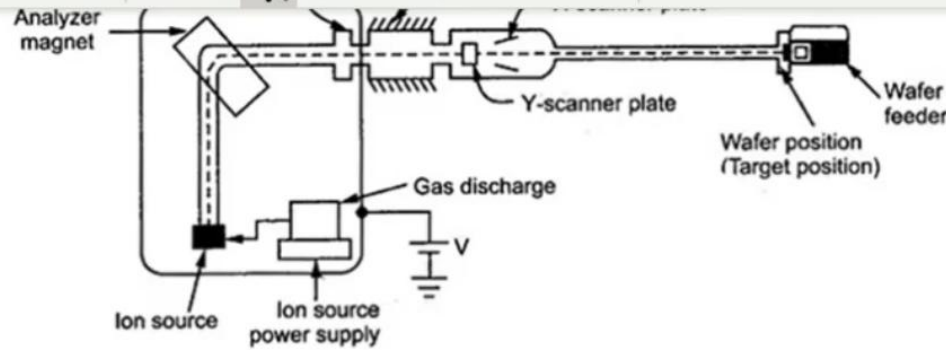
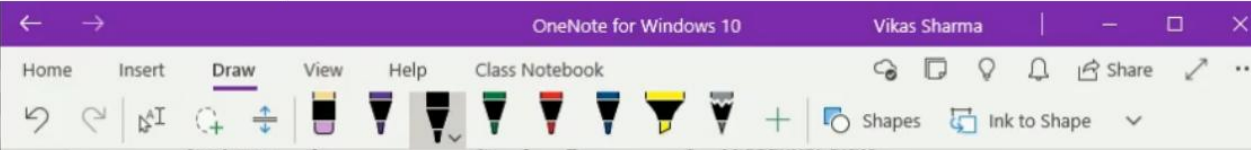
A dark gray rectangular box containing a red circle with a white letter 'D' inside it, and the text 'Dr. Vikas Sharma' below it.



Schematic diagram of typical ion-implanter



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Schematic diagram of typical ion-implanter

Table 4.1 Summary of the most common piezoresistor fabrication techniques: predeposition/diffusion, ion implantation and epitaxy

	Predeposition	Ion implantation	Epitaxy
Temperature (°C)	750–1100	750–1100	600–1100
Pressure	Atmospheric	High vacuum	Low vacuum
Throughput	High	High	Low
Lattice damage	Minimal	Substantial	Minimal
Concentration (cm ⁻³)	10 ²⁰ –10 ²¹	10 ¹⁶ –10 ²⁰	10 ¹⁶ –10 ²⁰
Min. t_j (nm)	<100	>500	<100
Masking materials	Hard mask	Hard/Soft mask	Hard mask
Profile modeling	Less complex	More complex	Less complex



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